Observation of Quantum Corrections to Conductivity of Disordered MoC and NbN Films up to Optical Frequencies

P. Neilinger<sup>1</sup>, S. Kern<sup>1</sup>, J. Greguš<sup>1</sup>, D. Manca<sup>1</sup>, B. Grančič<sup>1</sup>, M. Kopčík<sup>1</sup>, P. Szabó<sup>2</sup>, P. Samuely<sup>2</sup>, R. Hlubina<sup>1</sup>, and M. Grajcar<sup>1,3</sup>

<sup>1</sup>Department of Experimental Physics, Comenius University in Bratislava, Slovakia <sup>2</sup>Centre of Low Temperature Physics, IEP SAV, Košice, Slovakia <sup>3</sup>Institute of Physics, Slovak Academy of Sciences, Dúbravská cesta, Bratislava, Slovakia

#### Superconducting hybrids at Extreme, Štrbské pleso 28. 6. 2021

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- Need for a robust characterization method of the electric properties of disordered films in the metallic state

## Optical conductivity of metals

Drude model:

$$\sigma(\omega) = \sigma'(\omega) + i\sigma''(\omega) = \frac{\sigma_0}{1 - i\omega/\Gamma}$$

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#### Quantum correction to conductivity

Weakly disordered metals

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• Normal conductivity:

 $\sigma_{\rm reg}(\omega)\approx\sigma_0$ 

• Quantum correction  $\delta\sigma(\omega)$ :

- Weak-localization
- Interaction effects
- The same functional form
  - 3D:  $\delta\sigma(\omega) \sim \sqrt{\omega}$
  - 2D:  $\delta\sigma(\omega) \sim \ln(\omega)$



Temperature dependence

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- Generally considered low-temperature phenomena
- Theoretically should be present up to  $\omega^* \sim \Gamma$

#### Transport measurements at low temperatures

- Amorphous  $Nb_x Si_{1-x}$ , stoichiometry x tuning of disorder
- Resistivity measuremets from 20mK to 9K:

$$\sigma(T) = \sigma_0 + b\sqrt{T}$$



D.J. Bishop, E. G. Spencer, and R. C. Dynes, Solid State Electron. 38, 73 (1985)

#### Transport measurements of MoC

- $\blacksquare$  MoC, thickness tuned disorder
- $\blacksquare$  2D weak-localization and e-e interaction effects up to RT



J. Lee et al., PRB 49, 13882 (1994)

$$\sigma(T) = \sigma_0 + \{\alpha p + (1 - F)\} \ln(T)$$

- Magnetron sputtered in argon-acetylene atmosphere
- Mo target and sapphire substrates
- $Mo_x C_{1-x}$ ; stoichiometry (x) or thickness (t) tuned disorder
- Two sets of thin film samples:
  - 1. set:  $\mathbf{R}_{\Box}$  from 420 to 720  $\Omega$ ; fixed t=5 nm, varied x
  - **2**. set:  $\mathbf{R}_{\Box}$  from 100 to 220  $\Omega$ ; varied t, fixed x

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How far do they extend? The temperature range is limited.

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- for thin films:  $t \ll c/\omega,\, t \ll c|g(\omega)|/\omega,\,g',|g''| \lesssim 1$

$$\mathcal{T}(\omega) \approx \frac{\mathcal{T}_s(\omega)^2}{[1 + g'(\omega)/(n_s + 1)]^2 + [g''(\omega)/(n_s + 1)]^2}$$

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- Our experimental frequency range 80-1000 THz
- Spectroscopic ellipsometry
- Reflection measurement, evaluation of  $\sigma_1$  and  $\sigma_2$
- Our experimental frequency range 300-810 THz

#### Optical transmission spectra

- $\blacksquare$  1. set of MoC:  $\mathbf{R}_{\Box}$  = 420, 500, 590 a 720  $\Omega$
- Smooth transmission spectra



 $\blacksquare \ T(\omega)$  decreases with frequency  $\omega,$  the opposite is expected from the Drude model

















• Agreement between 3 data sets,  $\hbar\Omega \approx 14 \text{ meV}$  up to 4 eV

• Postulate for the  $\sigma$ :

$$\begin{split} \sigma'(\omega,T) &= \sigma_0 \left[ 1 - \mathcal{Q}^2 + \mathcal{Q}^2 \sqrt{\Omega/\Gamma} \right] & \text{if } \Omega < \omega^* \\ \sigma'(\omega,T) &= \frac{\sigma_0}{1 + (\Omega/\Gamma)^2} & \text{if } \Omega \ge \omega^* \end{split}$$

■ 3 parameters:

1. Q - "Quantumness"

2.  $\Gamma$  - Scattering rate

3.  $\sigma_0 = ne^2/m\Gamma$ , whereas  $\sigma(0,0) = \sigma_0(1-Q^2)$ 

• Fermi liquid theory, for interaction effects:

$$\Omega = \sqrt{\omega^2 + (\pi k_B T/\hbar)^2}$$

Imaginary part  $\sigma''$  given by Kramers-Kronig relations

- Contribution of bound electrons to permittivity

$$\sigma_{\text{bound}}''(\omega) = -\epsilon_0(\epsilon_\infty - 1)\omega, \ \epsilon_\infty = 1.4$$

# Conductivity $\sigma(\omega)$ fit



 Observation of quantum corrections to conductivity up to optical frequencies, Phys. Rev. B 100, 241106(R) (2019)

#### Smoothed Lorentzian model $\sigma(\omega)$

• Smoothing cups at  $\omega = \omega^*$ - "tailoring" with  $3^{rd}$ -order polynomial  $f(\omega)$  for  $\omega_- < \omega < \omega_+$ , for different  $\omega_-, \omega_+$ 



#### Extracted parameters of MoC with $R_{\Box} = 720\Omega$

#### Lorentz vs. Gaussian

	Drude		Gaussian	
$\epsilon_{\infty}$	1.0	1.4	1.0	1.4
$g_0 = Z_0 \sigma_0 d$	1.25	1.20	1.32	1.26
$Q^2$	0.66	0.65	0.68	0.67
$\hbar\Gamma$ (eV)	11.5	10.1	13.6	12.0
$n \ (10^{23} \ {\rm cm}^{-3})$	4.1	3.5	5.1	4.3

#### Smoothened Lorentzian

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• Scatter in  $\sigma_0$ , Q, and  $\Gamma \leq 15 \%$ 

 $\rightarrow$  Prolongation procedure is robust

•  $Q \approx 0.82 \pm 0.01$  strong quantum corrections  $\rightarrow \sigma'(0) = (1 - Q^2)\sigma_0 \approx \sigma_0/3$  $\rightarrow 3x$  reduced classical value

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ħΓ ≈ 11.85 ± 1.75 eV → explains the σ'(ω) ∝ √ω up to 4eV

• Normalized conductivity  $g_0 \approx 1.26 \pm 0.06$  $\implies n = (4.3 \pm 0.8) \times 10^{23} \text{ cm}^{-3}$ 

 $\rightarrow$  surprisingly large electron concentration

• Large  $\Gamma \implies$  Electronic bands separated by  $\leq \hbar \Gamma$  merge

- Concentration of Mo  $n_{\rm at} = 5.1 \times 10^{22} \ {\rm cm}^{-3}$
- Valence electron configuration within  $\pm \hbar \Gamma$  from  $\varepsilon_F$ Mo: 4d<sup>5</sup> 5s<sup>1</sup> a C: 2s<sup>2</sup> 2p<sup>2</sup>
- Corresponding electron density  $n = 10 \times n_{\text{at}} = 5.1 \times 10^{23} \text{ cm}^{-3}$ , in the range of the estimated  $n = (4.3 \pm 0.8) \times 10^{23} \text{ cm}^{-3}$

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- High Fermi energy  $\epsilon_F = 20.65, k_F l \approx 3.5$
- Similarly, highly disordered Nb<br/>N $n\approx 4.2\times 10^{23}~{\rm cm}^{-3}$
- Large n should be a generic property of dirty metals

#### Optical conductivity with the 2. set of MoC

■ Broad range of  $R_{\Box}$  =100, 120, 220, 420, 500, 590 a 720  $\Omega$ 



- Details of microstructure are not important
- The control parameter is the degree of disorder

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- Numerical extrapolation method for complex conductivity of disordered metals, S. Kern et al., PRB 103, 134205 (2021)



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### Optical transmission

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■ Transmission spectra from 0.5 to 6 eV

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#### Optical conductivity of NbN

- $\blacksquare$  Pulsed laser ablation; Nb-target, N2 atmosphere
- Film thickness t=3.5 nm and  $R_{\Box} = 655\Omega$



#### Numerical extrapolation of optical conductivity

Pulsed laser ablation; Nb-target, N<sub>2</sub> atmosphere
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Strong deviation from Drude-Lorentz model

- Observation of quantum corrections to conductivity up to optical frequencies in highly disordered films
- Method to extract  $\sigma_0$ ,  $Q \in \Gamma$  from the combined knowledge  $\sigma'(\omega)$  and  $\sigma''(\omega)$
- $\blacksquare$  Estimation of the magnitude of the quantum correction  $\delta\sigma' = -\mathcal{Q}^2\sigma_0$
- Numerical extrapolation method for complex conductivity of disordered metals

# Thank you for your attention!

Neilinger et al., Phys. Rev. B 100, 241106 (R) (2019)
S. Kern et al., Phys. Rev. B 103, 134205 (2021)